Mott-Anderson Metal-Insulator Transitions from Entanglement

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A metal can be driven to an insulating phase through distinct mechanisms. A possible way is via the Coulomb interaction, which then defines the Mott metal-insulator transition (MIT). Another possibility is the MIT driven by disorder, the so-called Anderson MIT. Here we analyze interacting particles in disordered Hubbard chains — thus comprising the Mott-Anderson physics — by investigating the ground-state entanglement with density functional theory. The localization signature on entanglement is found to be a local minimum at a certain critical density. Individually, the Mott (Anderson) MIT has a single critical density whose minimum entanglement decreases as the interaction (disorder) enhances. While in the Mott MIT entanglement saturates at finite values, characterizing partial localization, in the Anderson MIT the system reaches full localization, with zero entanglement, for sufficiently strong disorder. In the combined Mott-Anderson MIT, we find three critical densities referring to local minima on entanglement. One of them is the same as for the Anderson MIT, but now the presence of interaction requires a stronger disorder potential to induce localization. A second critical density is related to the Mott MIT, but due to disorder it is displaced by a factor proportional to the concentration of impurities. The third local minimum on entanglement is unique to the concomitant presence of disorder and interaction, found to be related to an effective density phenomenon, thus referred to as a Mott-like MIT. Since entanglement has been intrinsically connected to the magnetic susceptibility — a quantity promptly available in cold atoms experiments — our detailed numerical description might be useful for the experimental investigation of Mott-Anderson MIT.

I. INTRODUCTION

A metal can be transformed into an insulating system via different mechanisms. As proposed by Mott [1], the long-range character of the Coulomb interaction may lead to the metal-insulator transition (MIT). Also the short-range electron-electron interaction may induce MIT when there is one electron per lattice site, as proposed by Hubbard [2]. These transitions driven by interactions [3–5] are commonly referred to as Mott MIT. In the absence of interactions, the metal-insulator transition may alternatively be induced by disorder [6], the so-called Anderson MIT, due to coherent backscattering from randomly distributed impurities.

Theoretically, despite the difficulty to approach the MIT in solid systems, considerable progress has been achieved in cases where both disorder and electronic correlations play an important role [7–14]. However the interplay Mott-Anderson MIT is far from being completely understood. Besides, most of the studies applies dynamical mean-field theory (DMFT) [15], which allows the treatment of correlations and randomness on the same footing but is computationally demanding and restricted to rather simple systems.

A more general approach consists on exploring the differences between metal and insulator through the distribution of electrons in their many-body ground state, as qualitatively proposed by Kohn [16, 17] and more recently applied to the MIT context [18–22]. This then suggests that the electronic density function and other related density functional quantities, within density functional theory (DFT) [23], could be useful for describing MIT. Although it is well known that first-principles investigations via standard DFT methodology encounter considerable difficulty to recover the many-body gap, there are several proposals to correct this problem and improve the MIT description via DFT [24–31].

Moreover, recently DFT has been applied in the context of disordered superfluids to detect the superfluid-insulator transition (SIT) [32, 33]. In this case the transition was probed via entanglement, widely recognized as a powerful tool for identifying quantum phases transitions [34–38], including exotic states of matter [39–43]. Additionally, entanglement has been used to explore Mott MIT, without disorder [47–50]. Entanglement was also found to be intrinsically connected to the magnetic susceptibility [44–46], which is promptly available in cold atoms experiments and thus it could allow the experimental investigation of Mott-Anderson MIT.

In spite of that only a few studies uses entanglement to investigate Mott-Anderson MIT [51–53]. Refs. [51] and [52] adopt density matrix renormalization group (DMRG) techniques, numerically exact, but a highly costly method, in particular for disordered systems which require a large number of random disorder configurations. Ref. [53] uses instead an approximate DFT approach, allowing faster calculations, but the MIT was barely investigated, it was actually used as a test bed for the proposed analytical density functional for entanglement. Thus a deeper investigation of systems with Mott and Anderson physics via entanglement is still missing.

Here we apply DFT calculations to obtain entanglement and investigate the Mott-Anderson MIT in disordered Hubbard chains. We find that entanglement has a local minimum at a certain critical density related to the Mott and to the Anderson MIT individually. While the Mott-MIT entanglement minimum saturates at a finite value, characterizing a partially localized state,
We consider interacting fermions as described by the one-dimensional Hubbard model with on-site disorder,

\[ H = -t \sum_{\langle ij \rangle, \sigma} (\hat{c}_{i\sigma}^\dagger \hat{c}_{j\sigma} + h.c.) + U \sum_i \hat{n}_{i\uparrow} \hat{n}_{i\downarrow} + \sum_i V_i \hat{n}_{i\uparrow} \hat{n}_{i\downarrow}, \]  

where \( \hat{c}_{i\sigma}^\dagger (\hat{c}_{i\sigma}) \) is the creation (annihilation) operator and \( \hat{n}_{i\sigma} = \hat{c}_{i\sigma}^\dagger \hat{c}_{i\sigma} \) is the particle density operator, with spin component \( \sigma = \uparrow, \downarrow \) at site \( i \). The average density or filling factor is \( n = N/L \), where \( N = N_\uparrow + N_\downarrow \) is the total number of particles and \( L \) is the chain size. We adopt spin-balanced populations, \( N_\uparrow = N_\downarrow \), \( L = 100 \), open boundary conditions, zero temperature and \( U > 0 \). We express the local Coulomb interaction \( U \) and the disorder potential \( V_i \) in units of the hopping parameter \( t \), and set \( t = 1 \).

We consider pointlike impurities of strength \( V \) randomly distributed along the chain within a certain concentration \( C \% \), defined as \( C \equiv 100L_V/L \) where \( L_V \) is the number of impurity sites. To ensure results that are independent on specific configurations of impurities, we generate 100 samples for each set \( (C; V; U; n) \) of parameters, and thus all quantities analyzed here are an average over these 100 random disorder configurations. This huge amount of data makes it impracticable to use exact methods such as DMRG, so we apply instead DFT calculations for the Hubbard model (see [56–58] for a review on the accuracy of this formalism), obtaining the per-site ground-state energy \( e_0 \) and the density profile.

We explore the Mott-Anderson MIT via the average single-site entanglement, which is the entanglement between each site with respect to the remaining \( L-1 \) averaged over the sites. The ground-state entanglement of homogeneous \( (V = 0, L = \infty) \) chains can be quantified by the linear entropy,

\[ \mathcal{L}^{\text{hom}} = 1 - w_\uparrow^2 - w_\downarrow^2 - w_0^2, \]

where \( w_\uparrow = w_\downarrow = n/2 - \partial e_0 / \partial U \) are unpaired probabilities, \( w_2 = \partial e_0 / \partial U \) and \( w_0 = 1 - w_\uparrow - w_\downarrow - w_2 \) are paired and empty occupation probabilities. In this case the maximum entanglement, \( \mathcal{L} = 0.75 \), occurs when the four occupation states are equally probable: \( w_\uparrow = w_\downarrow = w_2 = w_0 = 1/4 \).

For the inhomogeneous (disordered and finite) chains, we thus adopt a well-established approximate density functional for the linear entropy \( \mathcal{L}^{\text{hom}}(n, U > 0) \) [53] to obtain entanglement via DFT within a local density approximation [54]

\[ \mathcal{L} \approx \mathcal{L}^{\text{DFT}} = \frac{1}{L} \sum_i \mathcal{L}^{\text{hom}}(n, U > 0)_{|n \rightarrow n_i}. \]  

This approach has also been successfully used recently to explore the superfluid-insulator transition in disordered superfluids [32, 33].
FIG. 2. Anderson metal-insulator transition driven by the density as probed by entanglement in clean (non interacting) nanostructures. For sufficiently strong disorder $V$ one finds a minimum entanglement at the critical density $n_V^C = 2C/100$ (in all curves $C = 50\%$). The minimum entanglement saturates at $\mathcal{L} = 0$ for $|V| \to \infty$, thus the system reaches a fully localized state.

The minimum appears at the critical density $n_V^C = 2C/100$ for $|V| \gtrsim 3t$. This critical $n_V^C$, first observed at the superfluid-insulator transition [32, 33], corresponds to the case where the number of impurity sites for $V < 0$ (non-impurity sites for $V > 0$) is equal to twice the number of particles. Thus the entanglement drop at $n_V^C$ characterizes the Anderson MIT: the attractive disorder freezes the degrees of freedom by favoring the double occupancy at the impurity sites (for $V > 0$ the non-impurity sites are doubly occupied at $n_V^C = 1 - 2C/100$).

But differently from the Mott case, in the Anderson MIT the system may reach a fully localized state if disorder is sufficiently strong to make $w_2 \to 1$ and thus $\mathcal{L}(|V| \to \infty) = 0$.

In Figure 3 we then turn on both disorder and interaction and investigate the impact of $U$ on the Anderson MIT and of $V$ on the Mott MIT. Fig. 3a shows that for small disorder strength ($V = -1t$) there is almost no influence on the Mott MIT: the minimum entanglement is maintained at $n_U^C = 1$ and the Anderson-MIT minimum at $n_V^C$ does not appear, as in the clean case. As $V$ increases, we observe the first impact of the disorder on the Mott MIT: the critical density for the Mott transition is displaced to $n_U^{C \to V} > 1$. This shift is reflecting the fact that the effective density in the metallic non-impurity sites, $n_{V=0}$, is smaller than $n$, since the particles are attracted to the $V < 0$ sites, such that it is necessary $n > 1$ to induce the Mott MIT at $n_{V=0} = 1$.

To determine $n_U^{C \to V}$ we start by considering that for $V < 0$ most of the particles accumulates in the attractive $L_V$ impurity sites (up to 2 per site, so $2L_V$ particles), thus leaving an effective $N - 2L_V$ number of particles in the remaining $L - L_V$ metallic sites. So the effective density can be defined as $n_{V=0} = (N - 2L_V)/(L - L_V)$ and the critical $n_U^{C \to V}$ will be then the average density $n$ for which $n_{V=0} = 1$. In terms of the concentration it can be written as

\[
1 = (N - 2L_V)/(L - L_V) \tag{4}
\]
\[
N = L + L_V \tag{5}
\]
\[
N/L = 1 + L_V/L \tag{6}
\]
\[
n_U^{C \to V} = 1 + C/100, \tag{7}
\]
TABLE I. Critical densities for metal-insulator transitions for $V < 0$ in the clean cases, $n_C^U$ for Mott and $n_C^V$ for Anderson, and in the combined Mott-Anderson MIT: $n_C^{U\leftrightarrow V}$ for the impact of $V$ in the $n_C^U$, $n_C^{V\rightarrow U}$ for the impact of $U$ in the $n_C^V$, and $n_C^{U\leftrightarrow V}$ for the Mott-like MIT that only appears in the presence of $V$ and $U$. For $V > 0$ the corresponding critical densities can be obtained via a particle-hole transformation, replacing the desired critical density $n_C \rightarrow \tilde{n}_C = 2 - n_C$.

<table>
<thead>
<tr>
<th>MIT</th>
<th>Densities</th>
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</thead>
<tbody>
<tr>
<td>Mott MIT</td>
<td>$n_C^U = 1$</td>
</tr>
<tr>
<td>$U \gtrsim 2t$, $V = 0$</td>
<td></td>
</tr>
<tr>
<td>Anderson MIT</td>
<td>$n_C^V = 2C/100$</td>
</tr>
<tr>
<td>$</td>
<td>V</td>
</tr>
<tr>
<td>Mott-Anderson MIT</td>
<td>$n_C^{U\rightarrow V} = 1 + C/100$</td>
</tr>
<tr>
<td>$U \gtrsim 2t$, $V \gtrsim 3t$</td>
<td>$n_C^{V\rightarrow U} = n_C^V = 2C/100$</td>
</tr>
<tr>
<td></td>
<td>$n_C^{U\leftrightarrow V} = C/100$</td>
</tr>
</tbody>
</table>

which agrees with the numerical results of Fig. 3.

Notice however that a similar effective density phenomenon occurs also for the impurity sites: for sufficiently strong $V < 0$, there will be an average density $n < 1$ for which the impurity-sites effective density, $n_V \equiv N/LV$, will be equal to 1, since $n = N/L < n_V$. This then means that there is another critical density $n_C^{U\rightarrow V} < 1$ associated to a Mott-like MIT – induced by the disorder – which in terms of the concentration is given by

$$1 = N/LV$$ \quad (8)

$$N/L = LV/L$$ \quad (9)

$$n_C^{U\rightarrow V} = C/100.$$ \quad (10)

Indeed we see in all curves of Fig. 3 a smoother minimum at $n_C^{U\rightarrow V}$ which was absent in the clean sites and is related to the Mott-like MIT induced by sufficiently strong disorder. Other effective-density features has been also reported for Hubbard chains in the presence of binary-alloy disorder [12]. Concerning the impact of the interaction on the Anderson MIT, Fig. 3a reveals that albeit the critical density remains at $n_C^V$, i.e., $n_C^{V\rightarrow U} = n_C^V = 2C/100$, the minimum entanglement is higher (compare it to the curve $V = -10t$ in Fig. 2). This then shows that in the presence of $U$ it is required a stronger disorder potential for localizing the system and, consequently, also for the full localization, marked by $\mathcal{L} = 0$. This comes from the fact that $U$ and $V$ contribute differently to the insulating phase: while $U > 0$ contributes by favoring the unpaired probabilities $(w_1, w_4)$, $V$ contributes by favoring the doubly-occupied probability $(w_2)$ [59]. Thus the competition between $U$ and $V$ requires a stronger disorder potential for the Anderson MIT. Accordingly, for the superfluid-insulator transition driven by disorder, where the attractive interaction $U < 0$ also favors the double occupancy, this competition effect is not observed [32, 33].

Fig. 3a also shows that for a fixed $V$, the minimum $\mathcal{L}$ at $n_C^{V\rightarrow U}$ becomes smaller for lower concentrations. This occurs because the critical density is smaller for lower $C$ and the impact of the interaction $U$ becomes less relevant for low densities, thus diminishing the $U$ and $V$ competition effect.

Fig. 3b confirms that by enhancing the disorder strength the system reaches the full localization at $n_C^{U\rightarrow V}$ even in the presence of $U$ for all the concentrations. We also find that for $n < n_C^{V\rightarrow U}$ entanglement increases but reaches a lower $\mathcal{L}$ platform in comparison to entanglement for $n > n_C^{V\rightarrow U}$. This phenomenon is related to the fact that for small densities the disorder hampers the connections among the particles, decreasing $\mathcal{L}$. Consistently, as $C$ enhances, the average distance among the impurity sites (for $V < 0$) decreases, and the platform becomes higher and broader.

Finally, we emphasize that all the MIT critical densities obtained here for attractive disorder, summarized in Table I, can be obtained for repulsive disorder by replacing the desired critical density $n_C \rightarrow \tilde{n}_C = 2 - n_C$ due to the particle-hole symmetry when changing from $-V$ to $+V$. This is confirmed by Fig. 3c, which shows the three entanglement minima at the replaced critical densities $-n_C^{U\rightarrow V} = 2 - 2C/100$ for the Anderson, $n_C^{U\rightarrow V} = 1 - C/100$ for the Mott and $n_C^{U\rightarrow V} = 2 - C/100$ for the Mott-like MIT – for the Mott-Anderson MIT of $V > 0$ disordered interacting systems.

IV. CONCLUSIONS

In summary, we have investigated the Mott-Anderson MIT via entanglement of interacting particles in disordered Hubbard chains. We find that entanglement is marked with a local minimum at the critical densities for which the MIT emerge, as summarized in Table I. While separately the Mott and Anderson MIT have only a single critical density each, for the combined Mott-Anderson MIT we find three distinct critical densities. One of them is the clean Anderson-MIT critical density, but the presence of interaction now requires a stronger disorder strength to localize the system with the same entanglement minimum. Another one is the clean Mott-MIT critical density but displaced by a factor proportional to the concentration of impurities. The third is a critical density exclusive from the interplay between disorder and interaction, and is found to be related to an effective density phenomenon, thus referred to as a Mott-like MIT.

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